

PROPERTIES OF Cd and Zn PARTIAL ELECTROLYTE TREATED CIGS SOLAR CELLS

K. Ramanathan, F. S. Hasoon, S. A. Smith, A. Mascarenhas, H. Al-Thani, J. Alleman, H. S. Ullal and J. Keane
National Renewable Energy Laboratory, 1617 Cole Boulevard, Golden CO 80401
P. K. Johnson and J. R. Sites
Physics Department, Colorado State University, Fort Collins CO 80523

ABSTRACT

We study the influence of Cd solution treatment on the photovoltaic properties of CuInGaSe_2 (CIGS) and CuInGaSSe_2 (CIGSS) thin film absorbers. We find that efficient solar cells can be fabricated by this method, and we compare their properties with those containing CdS window layers grown by chemical bath deposition. The results suggest that Cd plays a dominant role in establishing efficient photovoltaic junction in CuInSe_2 alloys. Micron scale photoluminescence scans show non-uniformity along the length probed. Cd treatment quenches one of the luminescence transitions and this indicates a change in shallow acceptor level population. We present a model by which we can explain the evolution of photovoltaic action.

INTRODUCTION

CuInSe_2 (CIS) thin films and their alloys with CuGaSe_2 and CuInS_2 have been the subject of study in the photovoltaic community because of their suitability for low cost power generation. Excellent cell efficiencies are demonstrated routinely in laboratory scale devices [1], and large area modules are entering the market place [2]. A majority of the laboratory scale devices are fabricated from CuInGaSe_2 (CIGS) alloys deposited by co-evaporation of the elements. Large area modules are made from $\text{CuInGa}(\text{SSe})_2$ absorbers (CIGSS) derived from sputtered metal precursors and subsequent reaction with the chalcogens. The two examples provide a sharp contrast in terms of the preparation of the absorber materials. In any further analysis of the physics of the devices, one must take into account the differences in the preparation methods and the resulting absorber properties. A reasonable starting point is that the absorbers are single phase, chalcopyrite $\text{Cu}(\text{In,Ga})(\text{SSe})_2$ alloy thin film where the Ga and/or S mole fractions are carefully controlled to be within tolerance limits, and the Cu composition is also controlled to avoid Cu chalcogenide impurities. In all of these materials, the junction formation is achieved by the growth of a thin CdS window layer by chemical bath deposition (CBD). CBD CdS processing produces the most efficient solar cells. However, the mechanism by which the junction is formed remains unclear. Historically, the CdS/CIGS interface has been

treated as "non-interacting" or an abrupt junction. There are a few reports [3,4] that suggest that the interface may be graded in composition, or may contain distinct compounds such as CdSe or CdIn_2Se_4 . The temperature of CBD growth is deceptively low, but the chemical driving forces are powerful enough to cause dissolution of species and cause atomic movements [5]. This is also illustrated in a case of aqueous treatment of CIS in In-S solutions where a thin CuInS_2 layer is grown on the surface [6]. Compositional changes such as those mentioned above have not been adequately treated in further analysis of the junction. A more serious omission is the potential role of electrically active impurities such as Cd or Zn which are known to produce efficient n-type conductivity [7] in the materials of interest. We have shown previously that the CBD reaction mixture containing only Cd, or a similar bath constituted with Zn, can be used to produce efficient photovoltaic cells in CuInSe_2 thin films [5]. In this report, we extend this work to high efficiency CIGS absorbers fabricated by the three stage process, and CIGSS absorbers provided by Shell Solar Industries (SSI).

EXPERIMENTAL

CIGS thin films were grown by the three stage process on Mo/soda lime glass substrates [8]. The resulting absorber material was 2.5 μm thick, and it was p-type with a hole density of $1\text{-}3 \times 10^{16} \text{ cm}^{-3}$. The nominal composition was $\text{CuIn}_{0.7}\text{Ga}_{0.3}\text{Se}_2$. The Cu concentration in the near-surface region was carefully controlled so that the overall $\text{Cu}/(\text{In}+\text{Ga})$ ratio is less than unity. Absorbers provided by SSI were graded CIGSS materials. CdS thin films were deposited from an aqueous solution containing 0.0015M CdSO_4 , 1.5M NH_4OH and 0.0075M thiourea. The temperature of the bath was raised from room temperature to 60 $^\circ\text{C}$ and the samples were held in the bath for 15 min. during which a 40-60 nm CdS film was deposited. Partial electrolyte treatments, designated as Cd PE and Zn PE, were performed by immersing the samples in a bath similar to the CdS deposition, but by excluding thiourea. The maximum temperature during the Cd PE treatment was 80 $^\circ\text{C}$ and the total immersion time was 22 min. Solar cells were fabricated by depositing a two-layer ZnO film. The first layer of 80-100 nm was deposited from a pure ZnO target, and the second layer of 200 nm was deposited from an Al_2O_3 doped target. Ni/Al con-

tacts were evaporated on the ZnO. Current-voltage characteristics of the solar cells were measured in dark and under light simulated to correspond to AM1.5 Global spectrum. Photoluminescence (PL) was excited by a He-Ne laser and collected by a InGaAs CCD array detector. The samples were held at 4K in a liquid He cold finger cryostat and the excitation level was about 120 nW.

RESULTS AND DISCUSSION

Fig. 1 shows the light current-voltage (J-V) characteristics of three types of solar cells fabricated from CIGS absorbers. Sputter deposition of ZnO directly on

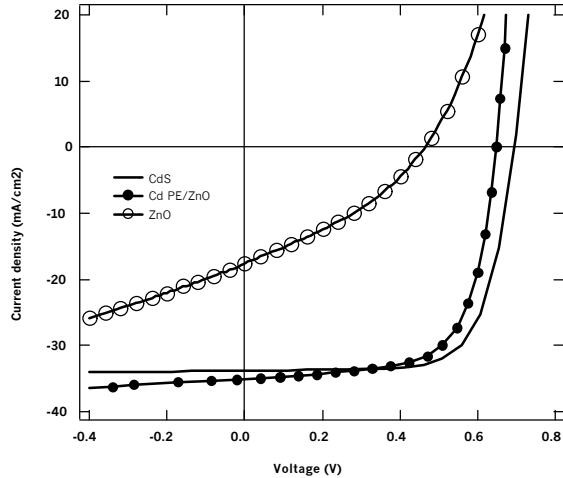


Fig. 1. Light J-V curves for solar cells fabricated on NREL CIGS absorbers.

the CIGS (open circles) does not produce a well behaved diode. The Cd PE treatment prior to the ZnO deposition (solid circles) results in a marked improvement, and an efficient solar cell is achieved. A comparison with the solar cell with a CdS window layer (solid line) demon-

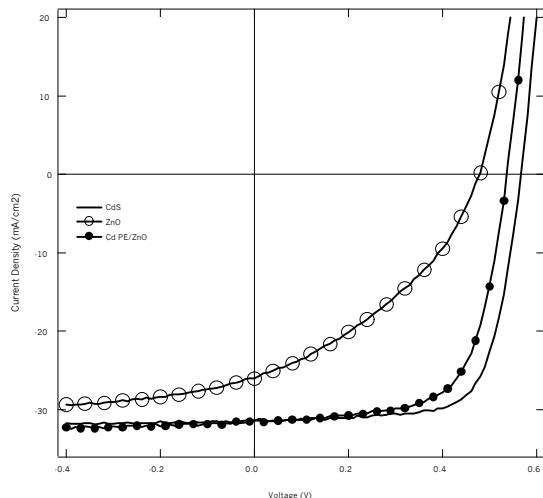


Fig. 2. Light J-V curves for a solar cells fabricated on SSI CIGSS graded absorbers.

strates the beneficial effect of Cd in creating a strong electric field within the device.

Fig. 2 is an example of these effects in CIGSS graded absorbers prepared by SSI in a manner that has no similarity to the CIGS absorbers. The trends are similar to the CIGS case, and demonstrate that Cd is equally effective in “real-world” materials.

The best solar cell made using Cd PE treatment has demonstrated a conversion efficiency of 15.7%. Another device made using Zn PE treatment produced a 14.2% solar cell. Both were characterized by NREL under standard reporting conditions. The solar cell parameters are shown in Table 1. These cells were fabricated from different absorbers and a direct comparison of the two cannot be made without taking into account the specific process details.

Table 1. Light J-V parameters of solar cells made using Cd PE and Zn PE. Device structure is ZnO/CIGS.

Treatment	V_{oc} (V)	J_{sc} (mA/cm ²)	FF	Efficiency (%)
Cd PE	0.636	34.64	0.72	15.7
Zn PE	0.558	36.28	0.7	14.2

Internal quantum efficiency of the Cd PE and CdS cells are shown in Fig. 3. The Cd PE cell exhibits a superior collection in the short wavelengths due to the absence of absorption and collection losses related to the CdS. The long wavelength response is maximized as well. Capacitance-voltage characteristics of the CdS and Cd PE cells were studied as a function of post heating after the deposition of CdS or Cd PE treatment. The carrier density profiles are changed by short anneals in air at 200 C. In the Cd PE cells, we have observed a lower carrier density and a flattening of the profile. The depletion width is also increased. This is likely the result of higher process temperature, and a consequent compensation of holes by Cd donors. The red response is enhanced as a result of field assisted collection. This aspect is discussed in another paper at this conference [9].

The current-voltage characteristics of two Cd PE cells are compared with a CdS cell in Fig. 4. A detailed analysis of the dark and light J-V characteristics was performed, and a summary is shown in Table 2. The reverse saturation current density of the Cd PE cell in the dark is two orders of magnitude higher than that of the CdS cell, and this difference is maintained under illumination as well. This can be ascribed to the higher interface

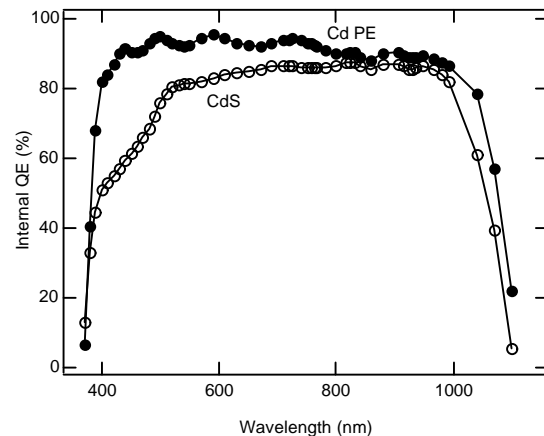


Fig. 3. Quantum efficiency of CIGS cells with CdS and Cd PE.

recombination velocity. The CdS deposition affords the growth of a lattice matched window layer, compositional grading at the interface, and passivation of interface states. The absence of these beneficial effects and the inclusion of a sputter deposited contact close to the high

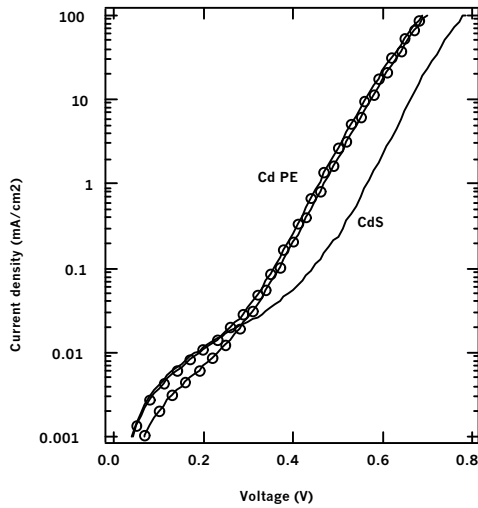


Fig. 4. Dark J-V characteristics of Cd PE and CdS solar cells.

field region can contribute to a higher J_0 in the Cd PE cells. These, coupled with the compensation of acceptors can explain the shortfall in the V_{oc} and fill factors of the Cd PE cells. However, the gap in performance between the two is smaller compared to the case where no Cd treatment is given, and this illustrates the dominant role Cd plays in the formation of the junctions.

Table 2. Diode quality factor, A, and reverse saturation current density, J_0 (A/cm^2), of CdS and Cd PE cells.

Type	A (dark)	J_0 (dark)	A (light)	J_0 (light)
CdS	1.7	10^{-9}	1.7	10^{-8}
Cd PE	1.9	10^{-7}	2.0	10^{-7}

In Figs. 5 and 6, we show the PL spectra of a CIGS thin film treated in ammonium hydroxide only and in Cd PE, respectively. The former is the baseline case, and is used as a “surface cleaning step” to remove accumulated alkali impurities. The excitation wavelength is 632.8 nm and it is strongly absorbed within the first quarter μm from the surface. The line scans are taken at 1 μm intervals over a 50 μm length.

There are two features to note. The PL intensities exhibit variation along the length probed, and this is attributed to the local variations in composition between the

grains and inter-grain regions. The spectral dependence shows two broad peaks centered around 1150 nm and 1250 nm for the ammonium hydroxide case. The higher energy emission is quenched by the action of Cd. Zott et al. [10] have shown that the PL emission peaks in CuInSe₂ thin films are donor-to-acceptor pair transitions. The quenching of the higher energy transition is signifi-

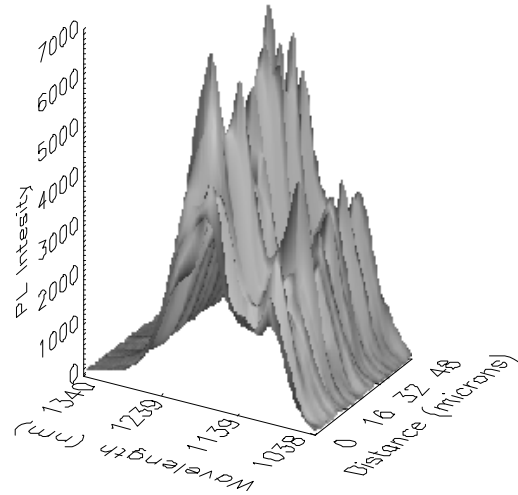


Fig. 5. PL spectrum of CIGS thin film treated in NH₄OH.

cant and can cause changes to the compensation ratio in CIGS. This is consistent with a similar observation made in CuInSe₂ single crystals where the electrical activity of Cd and Zn dopants was closely linked to changes in luminescence, and was associated with a downshift of the peak emission wavelength [11]. Given the complexity of the material, we are unable to say what defects are responsible for the changes.

In the above, we have shown a series of examples that clearly demonstrate the strong effect of Cd in creating efficient solar cells in CIS alloy thin films prepared by

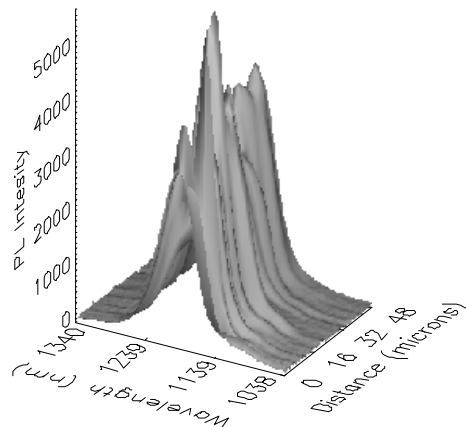


Fig. 6. PL spectra of CIGS thin film treated in Cd PE.

vastly different methods, i.e., co-evaporation and selenization. We attribute this to the ability of Cd and Zn to produce n-type doping. This is most logical explanation for the observed effects. Experimental evidence for this was provided in the studies of Cd and Zn diffusion in Cu-InSe₂ single crystals [7,11]. An appreciation of the differences between the single crystal devices and the present day thin film solar cells is essential. However, one must account for the effects that might be common to both. The evidence shown here suggests that the creation of an efficient n-type doping could well be at the heart of the CIS alloy thin film solar cells. The evolution of the solar cell can be viewed as a sequence of the following components:

Formation of Cd doped, n-type region in a p-CIGS absorber.

Compositional mixing and interface grading. Sulfur can play a useful role in passivating dangling bonds. This can minimize the effect of interface states and reduce the interface recombination velocity. Band discontinuities or spikes can be softened by grading. Shifting the peak of the electric field away from the metallurgical interface can also mitigate the effect of interface recombination.

Wide band gap window layer (CdS) protects the electrical junction from further processing, and provides field shaping within the n-region of the device.

It is clear that the optimal combination of all three would give rise to an efficient solar cell. Indeed, the same picture can be used to explain the behavior of solar cells made using Zn compounds in a CBD, CVD or ALE environments.

CONCLUSIONS

We have attempted to show that the high efficiency achieved in CBD CdS/ CIGS thin film solar cells arises from a set of key *interactions* that produce doping, compositional grading, and interface passivation. The results are shown to be applicable to laboratory samples and industrial scale samples from which modules are fabricated.

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